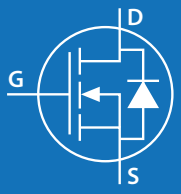
EPC2214 – Automotive 80 V (D-S) Enhancement Mode Power Transistor

V_{DS}, 80 V
$R_{DS(on)}$, 20 mΩ
I_D, 10 A,
AEC-Q101



EFFICIENT POWER CONVERSION

RoHS Halogen-Free

Revised April 25, 2025

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

Application Notes:

- Easy-to-use and reliable gate
- Gate Drive ON = 5-5.25 V typical, OFF = 0 V (negative voltage not needed)
- Top of FET is electrically connected to source

Questions:
Ask a GaN Expert

Maximum Ratings			
PARAMETER		**VALUE**	**UNIT**
V_{DS}	Drain-to-Source Voltage (Continuous)	80	V
I_D	Continuous (T_A = 25°C)	10	A
	Pulsed (25°C, T_{PULSE} = 10 µs)	60	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	–55 to 150	°C
T_{STG}	Storage Temperature	–55 to 150	

Thermal Characteristics			
PARAMETER		**TYP**	**UNIT**
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.7	°C/W
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	7.5	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	81	

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.
See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details

Static Characteristics (T_J = 25°C unless otherwise stated)						
PARAMETER		**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNIT**
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 0.2 mA	80			V
I_{DSS}	Drain-Source Leakage	V_{GS} = 0 V, V_{DS} = 64 V		0.003	0.15	mA
I_{GSS}	Gate-to-Source Forward Leakage	V_{GS} = 5 V		0.003	1.1	mA
	Gate-to-Source Forward Leakage#	V_{GS} = 5 V, T_J = 125°C		0.01	2.5	mA
	Gate-to-Source Reverse Leakage	V_{GS} = -4 V		0.003	0.15	mA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 2 mA	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	V_{GS} = 5 V, I_D = 6 A		15	20	mΩ
V_{SD}	Source-Drain Forward Voltage#	V_{GS} = 0 V, I_S = 0.5 A		1.9		V

Defined by design. Not subject to production test.
All measurements were done with substrate connected to source.



Die Size: 1.35 x 1.35 mm

EPC2214 eGaN® FETs are supplied only in passivated die form with solder bumps.

Applications

- Lidar/pulsed power applications
- DC-DC conversion
- Wireless power transfer

Benefits

- Ultra high efficiency
- Ultra low $R_{DS(on)}$
- Ultra low Q_G
- Ultra small footprint

Scan QR code or click link below for more information including reliability reports, device models, demo boards!

https://l.ead.me/EPC2214

Dynamic Characteristics# (T_J = 25°C unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 40 V		198	238	pF
C_{RSS}	Reverse Transfer Capacitance			1.8		
C_{OSS}	Output Capacitance			129	194	
$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	V_{GS} = 0 V, V_{DS} = 0 to 40 V		171		
$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			211		
R_G	Gate Resistance			0.65		Ω
Q_G	Total Gate Charge	V_{GS} = 5 V, V_{DS} = 40 V, I_D = 6 A		1.8	2.2	nC
Q_{GS}	Gate to Source Charge	V_{DS} = 40 V, I_D = 6 A		0.5		
Q_{GD}	Gate to Drain Charge			0.3		
$Q_{G(TH)}$	Gate Charge at Threshold			0.4		
Q_{OSS}	Output Charge	V_{GS} = 0 V, V_{DS} = 40 V		8	12	
Q_{RR}	Source-Drain Recovery Charge			0		

Defined by design. Not subject to production test.
All measurements were done with substrate connected to source.
Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.
Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.

Figure 1: Typical Output Characteristics at 25°C

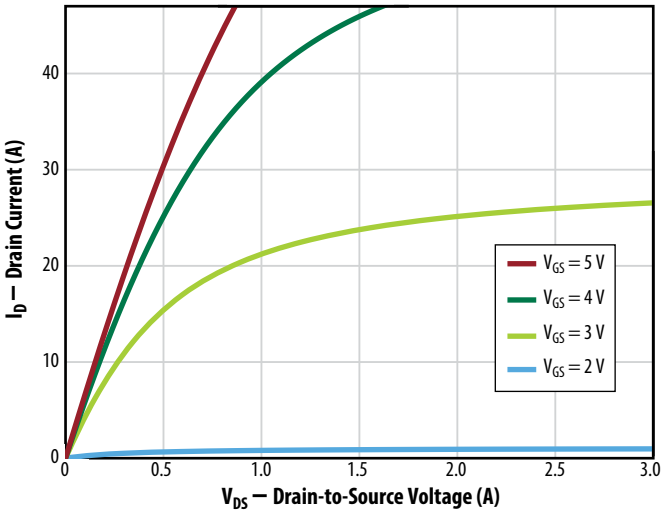


Figure 2: Typical Transfer Characteristics

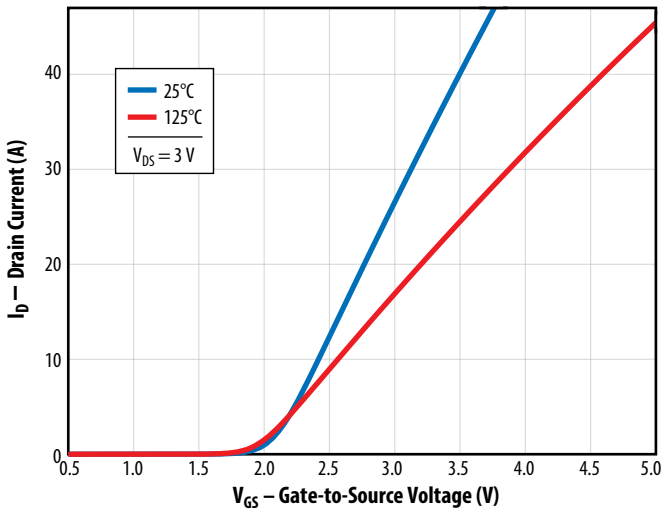


Figure 3: Typical $R_{DS(on)}$ vs. V_{GS} for Various Drain Currents

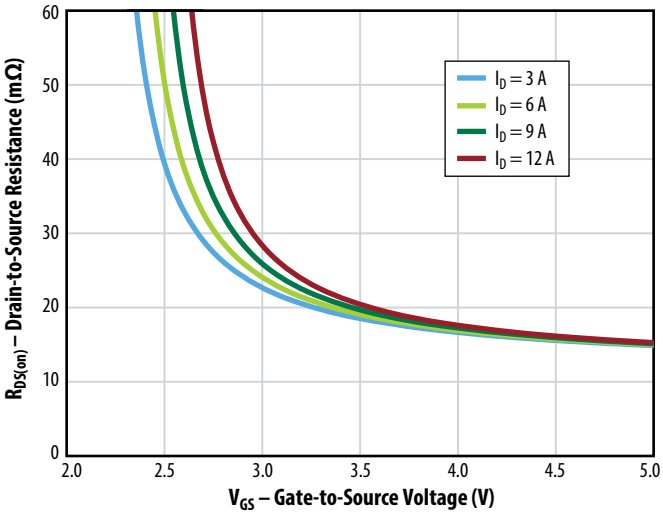


Figure 4: Typical $R_{DS(on)}$ vs. V_{GS} for Various Temperatures

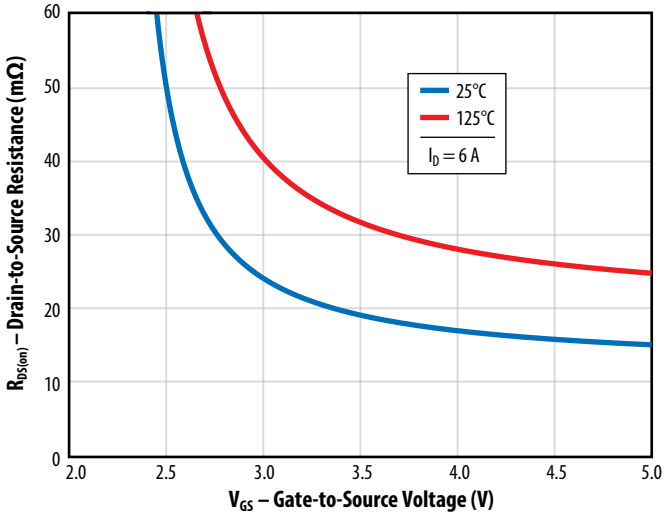


Figure 5a: Typical Capacitance (Linear Scale)

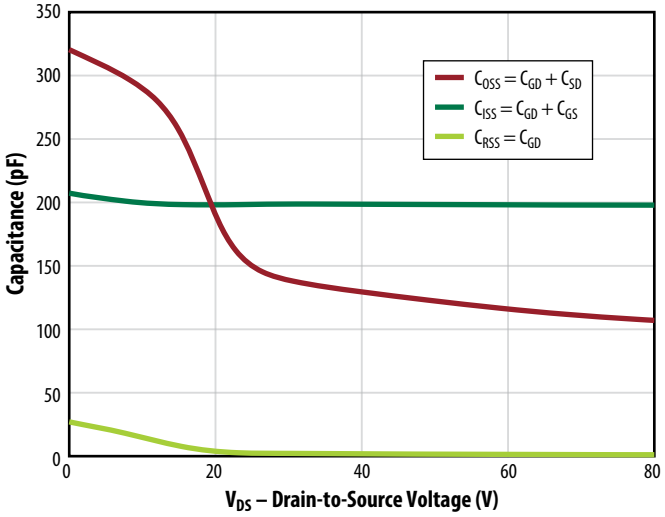


Figure 5b: Typical Capacitance (Log Scale)

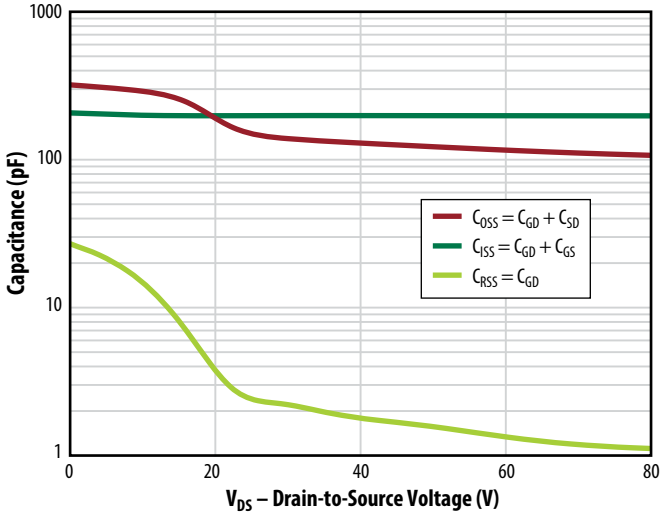


Figure 6: Typical Output Charge and C_{OSS} Stored Energy

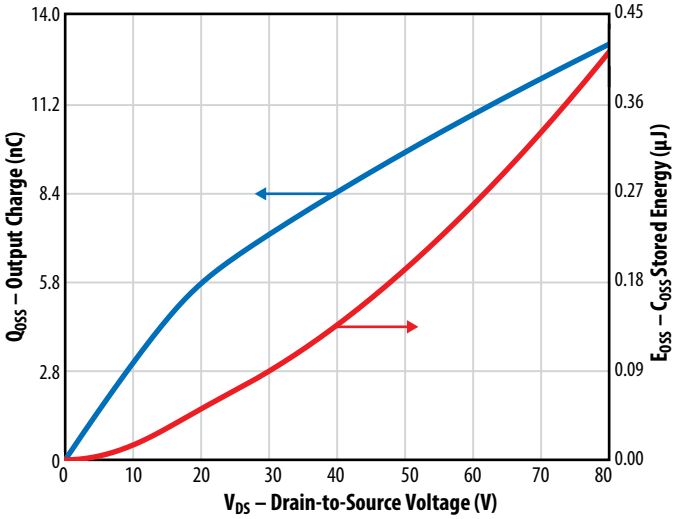


Figure 7: Typical Gate Charge

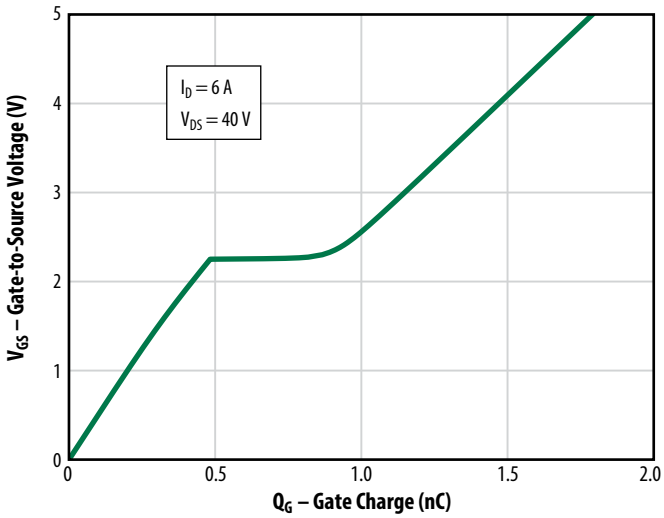
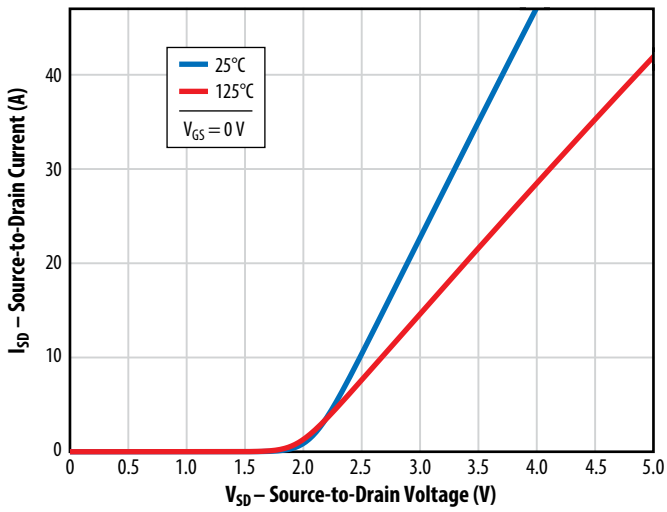


Figure 8: Typical Reverse Drain-Source Characteristics



Note: Negative gate drive voltage increases the reverse drain-source voltage. EPC recommends 0 V for OFF.

Figure 9: Typical Normalized On-State Resistance vs. Temp.

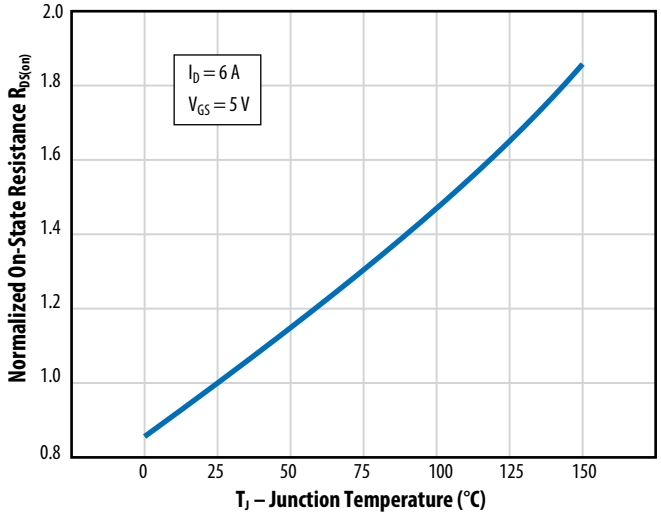


Figure 10: Typical Normalized Threshold Voltage vs. Temp.

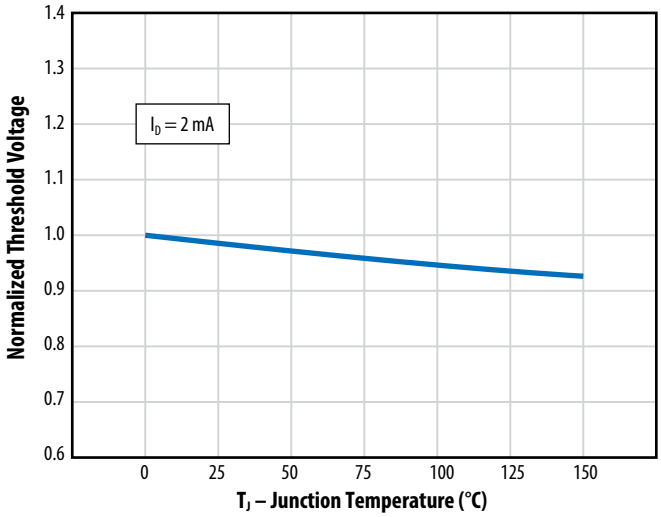
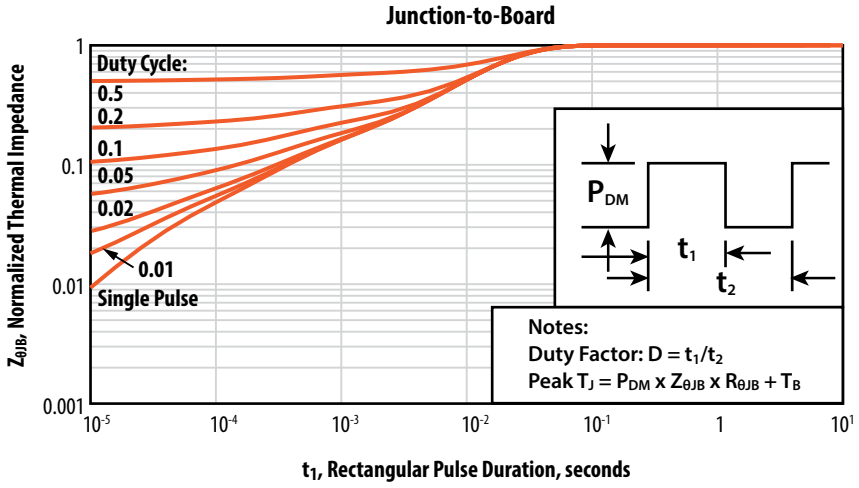


Figure 11: Typical Transient Thermal Response Curves



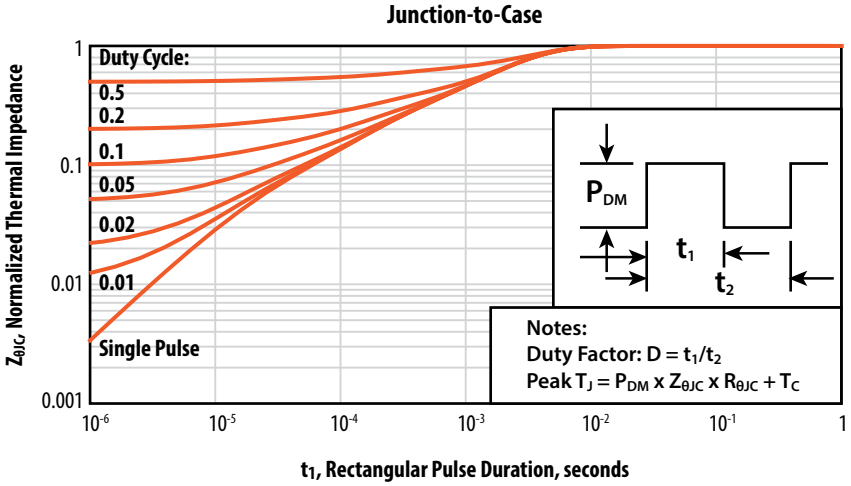
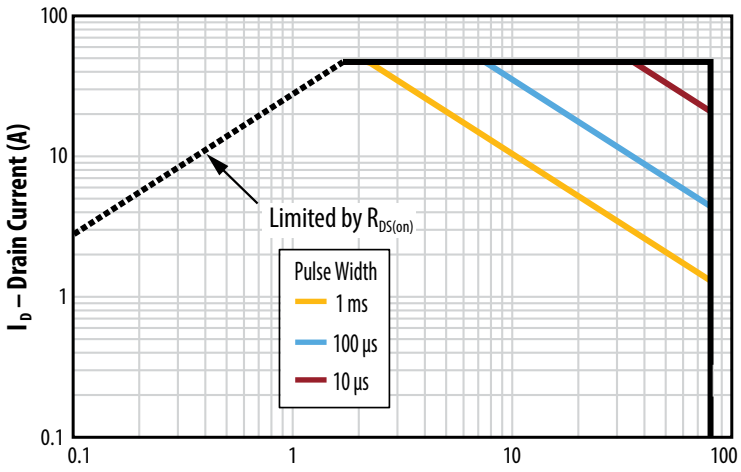


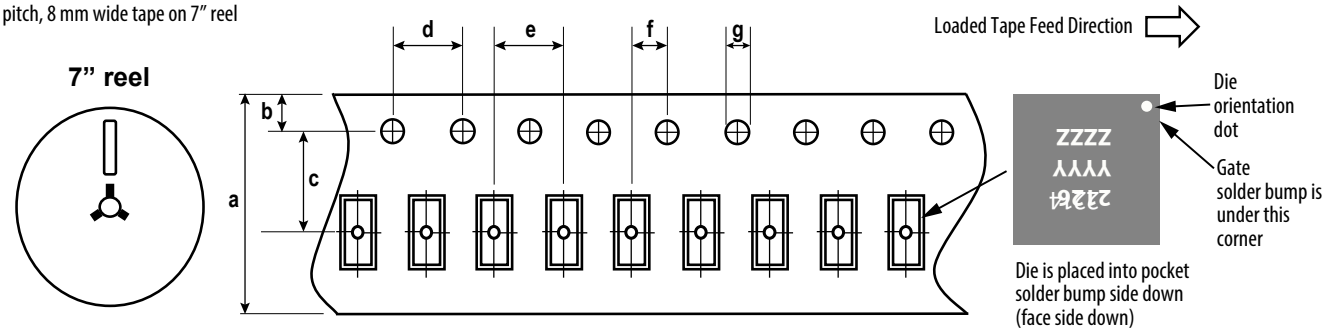
Figure 12: Safe Operating Area



T_J = Max Rated, T_C = +25°C, Single Pulse

TAPE AND REEL CONFIGURATION

4 mm pitch, 8 mm wide tape on 7" reel

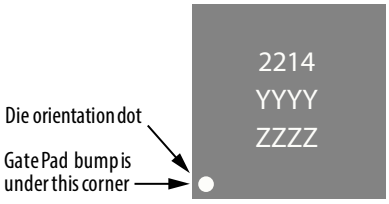


	Dimension (mm)		
EPC2214 (Note 1)	Target	MIN	MAX
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (Note 2)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (Note 2)	2.00	1.95	2.05
g	1.50	1.50	1.60

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.

Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

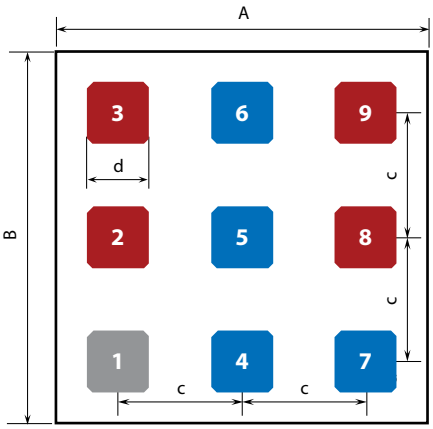
DIE MARKINGS



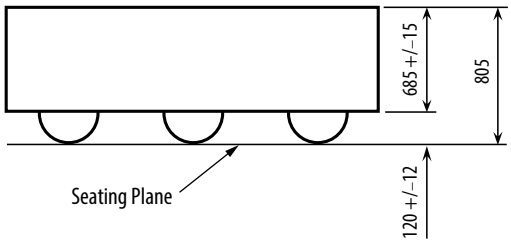
Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3
EPC2214	2214	YYYY	ZZZZ

DIE OUTLINE

Pad View



Side View

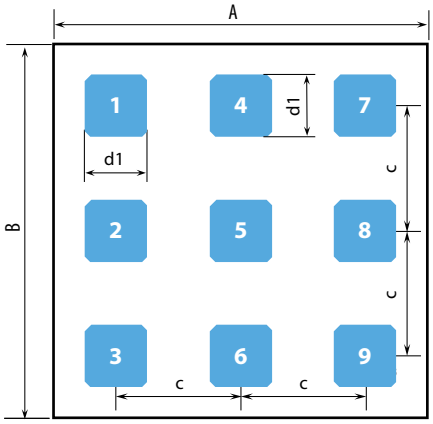


DIM	Micrometers		
	MIN	Nominal	MAX
A	1320	1350	1380
B	1320	1350	1380
c		450	
d		225	

Pad 1 is Gate;
Pads 4, 5, 6, 7 are Drain;
Pads 2, 3, 8, 9 are Source.

RECOMMENDED LAND PATTERN

(measurements in µm)



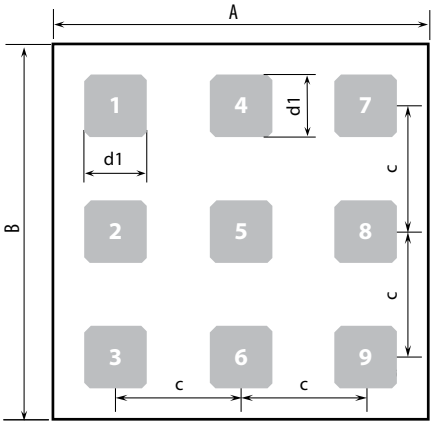
DIM	Micrometers
A	1350
B	1350
c	450
d1	205

The land pattern is solder mask defined.

Pad 1 is Gate;
Pads 4, 5, 6, 7 are Drain;
Pads 2, 3, 8, 9 are Source.

RECOMMENDED STENCIL DRAWING

(measurements in µm)



DIM	Micrometers
A	1350
B	1350
c	450
d1	225

Recommended stencil should be 4 mil (100 µm) thick, must be laser cut, openings per drawing.
The corner has a radius of R60.
Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources available at https://epc-co.com/epc/design-support

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